

Atty. Docket No. OF03P107/US
Serial No: 10/627,300

Amendment to the Abstract

Please replace the Abstract on pages 13-14 with the following replacement Abstract:

~~In a method for forming short-channel transistors, the method comprising the steps of: forming a first oxide layer and a sacrificial layer one after another on a semiconductor substrate and etching the sacrificial layer, thus forming a residual sacrificial layer pattern; conducting an ion implantation using the residual sacrificial layer pattern as a mask, thus forming an LDD ion implant layer in the semiconductor substrate; forming the first spacers on both side walls of the residual sacrificial layer pattern; conducting an ion implantation using the residual sacrificial layer pattern and the first spacers as a mask, thus forming a source/drain ion implant layer under the LDD ion implant layer; forming a nitride layer and a second oxide layer one after another on the whole surface of the former resultant object and conducting an annealing treatment, thus forming source/drain regions; conducting chemical-mechanical polishing (CMP) processes to the extent that an upper surface of the residual sacrificial layer pattern is exposed, and including removing the a residual sacrificial layer pattern used to mask an LDD ion-implant layer through etching; forming the second spacers on side walls of a portion where the residual sacrificial layer pattern is removed; conducting an ion implantation on the substrate between the second spacers, thus forming a punch-stop ion implant layer between the second spacers; etching the first oxide layer under the portion where the residual sacrificial layer pattern is removed, and forming a gate insulation layer, and forming a gate on the portion where the residual sacrificial layer pattern is removed.~~